Contents

Preface xi

SECTION I. MBE TECHNOLOGY

Twenty years of molecular beam epitaxy
A.Y. Cho 1

Less than 10 defects/cm$^2 \cdot \mu$m in molecular beam epitaxy grown GaAs by arsenic cracking
S. Izumi, N. Hayafuji, T. Sonoda, S. Takamiya and S. Mitsui 7

Arsenic-free GaAs substrate preparation and direct growth of GaAs/AlGaAs multiple quantum well without buffer layer
K. Iizuka, K. Matsumaru, T. Suzuki, H. Hirose, K. Suzuki and H. Okamoto 13

In-situ $Al_{0.24}Ga_{0.24}In_{0.52}As$ surface cleaning procedure using hydrogen radicals for molecular beam epitaxy regrowth
H. Künzel, R. Bochnia, J. Böttcher, P. Harde, A. Hase and U. Griebenow 18

Surface reconstructions and growth mode transitions of AlAs(100)
A.M. Dabiran and P.I. Cohen 23

Formation and characterization of GaAs/As superlattice grown by molecular beam epitaxy at low substrate temperature
T.M. Cheng, C.Y. Chang and J.H. Huang 28

Surface reconstruction of sulfur-terminated GaAs(001) observed during annealing process by scanning tunneling microscopy
S. Tsukamoto and N. Koguchi 33

Studies on interface roughness scattering effects in molecular beam epitaxy grown resonant tunneling structures
T. Hoshida, M. Tsuchiya, Y. Nakamura and T. Kamiya 38

Influence of growth related thickness fluctuations on the spectral and lateral luminescence intensity distribution in GaAs quantum wells
U. Jahn, K. Fujiwara, R. Hey, J. Kastrup, H.T. Grahn and J. Minniger 43

Observation of spatially-indirect transition and accurate determination of band offset ratio by excitation spectroscopy on GaAs/AlGaAs quantum wells lightly doped with Be acceptors
K. Muraki, S. Fukatsu, Y. Shiraki and Y. Takahashi 49

SECTION II. IN SITU CHARACTERIZATION

In situ film thickness and temperature control of molecular beam epitaxy growth by pyrometric interferometry
F.G. Boebel, H. Möller, B. Hertel, H. Grothe, G. Schraud, St. Schröder and P. Chow 54

Simultaneous monitoring of different surface processes on different streaks of the reflection high energy electron diffraction pattern
W. Braun and K. Ploog 62

Surface diffusion length of Ga adatoms in molecular-beam epitaxy on GaAs(100)-(110) facet structures
M. López and Y. Nomura 68

Surface flattening by annealing after molecular beam epitaxy growth revealed by in-situ secondary electron microscopy
J. Osaka, Y. Homma and N. Inoue 73

Reflection high-energy electron diffraction intensity oscillations during growth of (Al,Ga)As on GaAs(111)A
K. Sato, M.R. Fahy, I. Kamiya, J.H. Neave and B.A. Joyce 77

90° double reflection high-energy electron diffraction experiments on vicinal surfaces of GaAs
H. Nörenberg, L. Däweritz, P. Schützendübe, H.-P. Schönherr and K. Ploog 81

In-situ X-ray imaging of III–V strained-layer relaxation processes
C.R. Whitehouse, A.G. Cullis, S.J. Barnett, B.F. Usher, G.F. Clark, A.M. Keir, B.K. Tanner, B. Lunn, J.C.H. Hogg, A.D. Johnson, G. Lacey, W. Spirkl, W.E. Hagston, J.H. Jefferson, P. Ashu, G.W. Smith and T. Martin 85

In-situ second-harmonic generation study of the molecular beam epitaxy growth of GaAs
T. Kimura and C. Yamada 92

In-situ photoluminescence and capacitance–voltage characterization of InAlAs/InGaAs regrown heterointerfaces by molecular beam epitaxy
T. Saitoh, H. Tomozawa, T. Nakagawa, H. Takeuchi and H. Hasegawa 96
Structural transformation of As-stabilized surfaces caused by Ga-deposition detected by time-resolved surface photo-absorption
K. Uwai and N. Kobayashi 101
Nucleation of islands in GaAs molecular beam epitaxy studied by in-situ scanning electron microscopy
N. Inoue, J. Osaka and Y. Homma 107
Real-time scanning microprobe reflection high-energy electron diffraction observations of the cleaning process of GaAs substrates
Y. Morishita, S. Goto, Y. Nomura, T. Isu and Y. Katayama 110
Simultaneous reflection high-energy electron diffraction oscillations and mass spectroscopy investigations during molecular beam epitaxy growth of (001) GaAs – smooth surfaces or stoichiometric films?
Ch. Heyn and M. Harsdorff 117
Role of the substrate deoxidation process in the growth of strained InAs/InP heterostructures
M.R. Bruni, N. Gambacorti, S. Kačiulis, G. Mattogno, M.G. Simeone, L.G. Quagliano, N. Tomassini and B. Jusserand 123

SECTION III. STM, AFM AND GROWTH KINETICS

Studies of large scale unstable growth formed during GaAs(001) homoepitaxy
C. Orme, M.D. Johnson, K.-T. Leung, B.G. Orr, P. Smilauer and D. Vvedensky 128
Surface structure of GaAs(001)-(2 × 4) α, β and γ phases
A. Ichimiya, Q.-K. Xue, T. Hashizume and T. Sakurai 136
GaAs initial growth on InAs (001) vicinal surfaces observed by scanning tunneling microscopy
N. Ikoma and S. Ohkouchi 144
Unified model for first-order transition and electrical properties of InAs (001) surfaces based on atom-resolved scanning tunneling microscopy imaging
H. Yamaguchi and Y. Horikoshi 148
Atomic force microscope observation of the initial stage of InAs growth on GaAs substrates
H. Kitabayashi and T. Waho 152
Theoretical investigation of adsorption behavior during molecular beam epitaxy growth of GaAs: ab initio based microscopic calculation
K. Shiraishi and T. Ito 158
Ab initio study on the As-stabilized surface structure in AlAs molecular beam epitaxy
Y.S. Hiraoka and M. Mashita 163
Kinetic Ising model of site-correlated adsorption and surface diffusion in molecular-beam epitaxy
H. Nakayama, M. Tochigi, H. Maeda and T. Nishino 168
Molecular dynamics simulation of (100)InGaAs/GaAs strained-layer relaxation processes
P.A. Ashu, J.H. Jefferson, A.G. Cullis, W.E. Hagston and C.R. Whitehouse 176
Diffusion constant of Ga adatom on GaAs (001) surface: molecular dynamics calculations
A. Palma, E. Semprini, A. Talamo and N. Tomassini 180
Indium surface segration in InGaAs-based structures prepared by molecular beam epitaxy and atomic layer molecular beam epitaxy
A. Bosacchi, F. Colonna, S. Franchi, P. Pascarella, P. Allegri and V. Avanzini 185
Role of step orientation and step–step interaction in the in-situ creation of laterally confined semiconductor nanostructures via growth: a simulated annealing study on a parallel computing platform
R. Viswanathan, A. Madhukar and S.B. Ogale 190

SECTION IV. DOPING

The characterization of the growth of sub-monolayer coverages (1/200th to 1 monolayer) of Si and Be on GaAs(001): a reflectance anisotropy spectroscopy and reflection high-energy electron diffraction study
D.A. Woolf, K.C. Rose, S.J. Morris, D.I. Westwood, J. Rumberg, F. Reinhardt, W. Richter and R.H. Williams 197
A scanning tunnelling microscopy study of the deposition of Si on GaAs(001); implications for Si δ-doping
A.R. Avery, D.M. Holmes, J.L. Sudijono, T.S. Jones, M.R. Fahy and B.A. Joyce 202
Diffusion of Si-acceptor in δ-doped GaAs grown on GaAs(111)A by molecular beam epitaxy
M. Hirai, H. Ohnishi, K. Fujita, P. Vaccaro and T. Watanabe 209

Atomic-scale controlled incorporation of ultrahigh-density Si doping sheets in GaAs
L. Däweritz, H. Kostial, R. Hey, M. Ramsteiner, J. Wagner, M. Maier, J. Behrend and M. Höricke 214
Heavily carbon-doped p-type (In)GaAs grown by gas-source molecular beam epitaxy using diiodomethane
T. Tomioka, N. Okamoto, H. Ando, S. Yamaura and T. Fujii 221
Tin as an n-type dopant in the molecular beam epitaxial growth of GaAs(111)A
S.J. Hu, M.R. Fahy, K. Sato and B.A. Joyce 227
Se-doped AlGaAs grown on GaAs(111)A by molecular beam epitaxy
H. Ohnishi, M. Hirai, T. Yamamoto, K. Fujita and T. Watanabe 231
Carbon doping into GaAs using combined ion beam and molecular beam epitaxy method
T. Iida, Y. Makita, S. Kimura, Y. Kawasumi, A. Yamada, S. Uekusa and T. Tsukamoto 236
Carbon background in P-based III–V semiconductors grown by metalorganic molecular beam epitaxy using ethyl-metalorganic sources
M. Yoshimoto, S. Tanaka, T. Tsuji, H. Kurata, K. Nishimura and H. Matsunami 241
p-Type GaAs doped by diiodomethane (CI_2H_2) in molecular beam epitaxy, metalorganic molecular beam epitaxy, and chemical beam epitaxy
N.Y. Li, H.K. Dong, C.W. Tu and M. Geva 246
High carbon doping of $Ga_{1-x}In_xAs$ ($x \approx 0.01$) grown by molecular beam epitaxy
A. Mazuelas, M. Maier, J. Wagner, A. Trampert, A. Fischer and K.H. Ploog 251
The injected carbon impurities in intermixed GaAs/AlAs multiple quantum wells during thermal treatment
Y.T. Oh, S.K. Kim, S.C. Byun, T.W. Kang, C.Y. Hong, J.J. Lee, H.K. Lee and T.W. Kim 256
Shallow donors and deep levels in GaAs grown by atomic layer molecular beam epitaxy
A. Bosacchi, E. Gombia, R. Mosca, S. Franchi, A. Carnera and A. Gasparotto 261
Quantum transport measurements on Si δ- and slab-doped $In_{0.53}Ga_{0.47}As$ grown by molecular beam epitaxy
M. McElhinney, E. Skuras, S.N. Holmes, E.A. Johnson, A.R. Long and C.R. Stanley 266
Negative magnetoresistance in Si atomic-layer-doped GaAs
H. Goto, W. Shi, T. Suzuki, N. Sawaki, H. Ito and K. Hara 271

SECTION V. QUANTUM WIRES AND BOXES

New frontiers of molecular beam epitaxy with in-situ processing
M. Hong 277
GaAs/AlGaAs quantum wire lasers fabricated by cleaved edge overgrowth
W. Wegscheider, L.N. Pfeiffer, A. Pinczuk, K.W. West, M.M. Dignam, R. Hull and R.E. Leibenguth 285
Strained AlGaInP quantum wire lasers
P.J. Pearah, A.C. Chen, A.M. Moy, K.C. Hsieh and K.Y. Cheng 293
$In_xGa_{1-x}As$/GaAs quantum wire structures grown on GaAs (100) patterned substrates with [100] ridges
Y. Liu, N. Yamamoto, Y. Nishimoto, N. Kamikubo, S. Shimomura, K. Gamo, K. Murase, N. Sano, A. Adachi, K. Fujita, T. Watanabe and S. Hiyamizu 299
Direct molecular beam epitaxial growth of low-dimensional structures on reactive ion etched surfaces
T. Röhr, H. Kratzer, G. Böhm, W. Klein, G. Tränkle and G. Weimann 306
In-situ fabrication of three-dimensionally confined GaAs and InAs volumes via growth on non-planar patterned GaAs(001) substrates
A. Konkar, K.C. Rajkumar, Q. Xie, P. Chen, A. Madhukar, H.T. Lin and D.H. Rich 311
Self-formation of 100 nm scale wire structures during molecular beam epitaxial growth of AlGaAs on patterned substrates
Y. Kadoya, T. Yoshida, Y. Nagamune, H. Noge and H. Sakaki 317
Control of ridge shape for the formation of nanometer-scale GaAs ridge quantum wires by molecular beam epitaxy
S. Koshiba, T. Noda, H. Noge, Y. Nakamura, H. Ichinose, T. Shitara, D.D. Vvedensky and H. Sakaki 322
Fabrication of InGaAs ridge quantum wires by selective molecular beam epitaxy and their characterization
H. Fujikura and H. Hasegawa 327
Fabrication of GaAs quantum wires by metalorganic molecular beam epitaxy and their optical properties
Y. Nomura, S. Goto, Y. Morishita, I. Matsuyama and Y. Katayama 332
Organized growth of GaAs/AlAs lateral structures on atomic step arrays: what is possible to do?
B. Etienne, F. Laruelle, J. Bloch, L. Sfaxi and F. Lelarge 336
InGaAs/InAlAs in-plane superlattices grown on slightly misoriented (110) InP substrates by molecular beam epitaxy
Y. Nakata, O. Ueda, A. Tackeuchi, S. Nakamura and S. Muto 341
Transmission electron microscopic evaluation of InGaAs/InAlAs in-plane superlattices grown on slighly misoriented (110)InP substrates by molecular beam epitaxy
O. Ueda, Y. Nakata, A. Takeuchi, S. Nakamura and S. Muto 346

Optical investigation of the self-organized growth of InAs/GaAs quantum boxes
J.M. Gérard, J.B. Génin, J. Lefebvre, J.M. Moison, N. Lebouché and F. Barthe 351
Realization of optically active strained InAs island quantum boxes on GaAs(100) via molecular beam epitaxy and the role of island induced strain fields
Q. Xie, P. Chen, A. Kalburge, T.R. Ramachandran, A. Nayfonov, A. Konkar and A. Madhukar 357
Optimized InAs quantum effect device structures grown by molecular beam epitaxy
K. Yoh, H. Takeuchi, A. Nishida and M. Inoue 364

SECTION VI. PATTERNED GROWTH AND SELECTIVE GROWTH

Selective growth and other applications of hydrogen-assisted molecular beam epitaxy
M. Kawabe 370
Selective area growth of GaAs using a Ga beam with a step-function lateral intensity profile
N. Tomita, N. Yoshida, S. Shimomura, K. Murase, A. Adachi and S. Hiyamizu 377
Electrical properties of lateral npn junctions using molecular beam epitaxy grown Si-doped GaAs on patterned substrates
T. Takamori and T. Kamijoh 383
Transmission electron microscopy observation of GaAs/$Al_{0.3}Ga_{0.7}As$ T-shaped quantum well structure fabricated by glancing angle molecular beam epitaxy on GaAs(100) reverse-mesa etched substrates
M. Tanaka, N. Tomita, T. Higuchi, S. Shimomura, A. Adachi, N. Sano and S. Hiyamizu 388
Dependence of InP and GaAs chemical beam epitaxial growth rate on substrate orientations; applications to selective area epitaxy
P. Legay, F. Alexandre, J.L. Benchimol and J.C. Harmand 394
Symmetric InP mirror facets fabricated by selective chemical beam epitaxy on reactive-ion-etched sidewalls
M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita 399
Stability of GaAs oxide under metalorganic molecular beam epitaxy process
Y. Hiratani, M. Sasaki, S. Yoshida and M. Yamada 404

SECTION VII. GROWTH ON (*N*11) AND (110) GaAs SUBSTRATES

Extremely flat interfaces in GaAs/AlGaAs quantum wells with high Al content (0.7) grown on GaAs (411)A substrates by molecular beam epitaxy
S. Shimomura, S. Kaneko, T. Motokawa, K. Shinohara, A. Adachi, Y. Okamoto, N. Sano, K. Murase and S. Hiyamizu 409
Characterization of GaAs/AlAs interfacial atomic step structures on a (411)A-oriented substrate by transmission electron microscope
Y. Tsuda, S. Shimomura, S. Hiyamizu and N. Sano 415
Evaluation of the highly coherent surface structure of the GaAs (411)A plane using scanning tunneling microscopy
T. Yamada, H. Yamaguchi and Y. Horikoshi 421
Scanning tunneling microscopy of the GaAs (311)A surface reconstruction
M. Wassermeier, J. Sudijono, M.D. Johnson, K.T. Leung, B.G. Orr, L. Däweritz and K. Ploog 425
Optical anisotropy of (11*N*) and vicinal (001) quantum wells
Y. Kajikawa, O. Brandt, K. Kanamoto and N. Tsukada 431
Strong enhancement of the optical and electrical properties, and spontaneous formation of an ordered superlattice in (111)B AlGaAs
A. Chin, H.Y. Lin and K.Y. Hsieh 436
Structural analysis of AlGaAs quantum wires on vicinal (110)GaAs by transmission electron microscopy and energy dispersive X-ray spectroscopy
M. Takeuchi, K. Shiba, H.K. Huang, K. Sato, K. Inoue, K. Maehashi and H. Nakashima 441
Molecular beam epitaxy growth and properties of GaAs/(AlGa)As p-type heterostructures on (100), (011), (111)B, (211)B, (311)B, and (311)A oriented GaAs
M. Henini, P.A. Crump, P.J. Rodgers, B.L. Gallagher, A.J. Vickers and G. Hill 446
The growth and physics of ultra-high-mobility two-dimensional hole gas on (311)A GaAs surface
M. Henini, P.J. Rodgers, P.A. Crump, B.L. Gallagher and G. Hill 451
Silicon compensation and scattering mechanisms in two-dimensional electron gases on (110)GaAs
M.C. Holland, A.H. Kean and C.R. Stanley 455

SECTION VIII. STRAINED LAYER STRUCTURES AND InP BASED STRUCTURES

Surfactant-mediated molecular-beam epitaxy of III–V strained-layer heterostructures
E. Tournié, N. Grandjean, A. Trampert, J. Massies and K.H. Ploog 460

Growth of InGaAs/GaAs heterostructures with abrupt interfaces on the monolayer scale
J.-M. Gérard and C. d'Anterroches 467
Effects of alloy composition on the As desorption from and adsorption on strained $In_xGa_{1-x}As$ surfaces
M.J. Ekenstedt, H. Yamaguchi and Y. Horikoshi 473
Magnitude and polarity of strain-induced fields in pseudomorphic $In_{0.2}Ga_{0.8}As$ quantum well structures on (112) GaAs substrates
D. Sun, R.H. Henderson and E. Towe 478
Aspects of low heterostructure symmetry in (311)A (In,Ga)As/GaAs
M. Ilg, M.I. Alonso, A. Mazuelas, E. Tournié and K.H. Ploog 482
Preferential migration of indium atoms on the (411)A plane in InGaAs grown on GaAs channeled substrates by molecular beam epitaxy
T. Kitada, A. Wakejima, N. Tomita, S. Shimomura, A. Adachi, N. Sano and S. Hiyamizu 487
Non-linear As(P) incorporation in $GaAs_{1-y}P_y$ on GaAs and $InAs_{1-y}P_y$ on InP
J.E. Cunningham, M.D. Williams, R.N. Pathak and W. Jan 492
Effect of atomic hydrogen in highly lattice-mismatched molecular beam epitaxy
Y.J. Chun, Y. Okada and M. Kawabe 497
Strain relaxation in InGaAs/GaAs quantum wells grown on GaAs (111)A substrates
P.O. Vaccaro, M. Takahashi, K. Fujita and T. Watanabe 503
Precise thickness measurement within a few monolayers by X-ray diffraction from InGaAs/GaAs strained-layer superlattices
M. Sato, T. Kawaguchi and S. Nishi 508
Phonon behavior and interfacial stress in the strained $(InAs)_m/(GaAs)_n$ ultrathin superlattices
S. Emura, Y. Matsui and S. Gonda 513
Molecular beam epitaxial growth and thermodynamic analysis of InGaAs and InAlAs lattice matched to InP
M. McElhinney and C.R. Stanley 518
Generation mechanism of CuAu-I type ordered structures in InGaAs crystals grown on (110) InP substrates by molecular beam epitaxy
O. Ueda, Y. Nakata and S. Muto 523
Effect of As_i on the optical properties of $Ga_{1-x}In_xAs/InP$ grown by molecular beam epitaxy
M. Popp, M. Schiefele, M. Hurich, M. Wachter, J.M. Schneider, B. Marheineke and H. Heinecke 528
Effects of substrate misorientation on triple-period ordering in AlInAs
A. Gomyo, K. Makita, I. Hino and T. Suzuki 533

SECTION IX. GSMBE, MOMBE AND CBE

Chemical beam epitaxial growth of high optical quality AlGaAs – the influence of precursor purity on material properties
R.W. Freer, T. Martin, P.A. Lane, C.R. Whitehouse, T.J. Whitaker, M. Houlton, P.D.J. Calcott, D. Lee, A.C. Jones and S.A. Rushworth 539
Effects of cation diffusion during chemical etching
T.H. Chiu, W.T. Tsang, M.D. Williams, C.A.C. Mendonça, K. Dreyer and F.G. Storz 546
Low temperature etching of GaAs substrates and improved morphology of GaAs grown by metalorganic molecular beam epitaxy using trisdimethylaminoarsenic and triethylgallium
D. Marx, H. Asahi, X.F. Liu, M. Higashiwaki, A.B. Villaflor, K. Miki, K. Yamamoto, S. Gonda, S. Shimomura and S. Hiyamizu 551
Reduction of carbon incorporation in the in-situ selective-area epitaxy of GaAs by metalorganic molecular beam epitaxy using tris-dimethylaminoarsine
S. Yoshida and M. Sasaki 557
Selectively regrown carbon-doped (Al)GaAs by chemical beam epitaxy with novel gas sources
N.Y. Li, Y.M. Hsin, H.K. Dong, T. Nakamura, P.M. Asbeck and C.W. Tu 562
Selective-area epitaxial growth of GaAs by gas-source molecular-beam epitaxy using metal gallium and trisdimethylaminoarsine
S. Goto, C. Jelen, Y. Nomura, Y. Morishita and Y. Katayama 568
Gas source molecular beam epitaxial growth of GaP/AlP modulated superlattices and their optical properties
J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim, T. Ogura and S. Gonda 574
Gas source molecular beam epitaxy grown InGaAsP/InGaAlAs multi-quantum well structures with wide range continuum band-offset control
K. Makita, A. Gomyo and I. Hino 579

Characterization of heavily carbon-doped GaAs with a hole concentration of the order of 10^{21} cm^{-3} grown by metalorganic molecular beam epitaxy and its application to InGaP/GaAs heterojunction bipolar transistors
J. Shirakashi, T. Azuma, F. Fukuchi, M. Konagai and K. Takahashi 585
Effect of source-supply interruptions on the interface abruptness in gas source molecular beam epitaxy grown InGaAs/InP heterostructures
T. Mozume, H. Kashima, K. Hosomi, K. Ouchi, H. Sato, H. Masuda and T. Tanoue 591
InGaAsP/InAlAs type I/type II multiple quantum well structures grown by gas source molecular beam epitaxy
Y. Kawamura and H. Iwamura 597
A new method of flux calibration for gas source molecular beam epitaxy of InP and its application to migration enhanced epitaxy
T. Ozeki, B.X. Yang and H. Hasegawa 602
Gas-source molecular beam epitaxy of lattice-matched $Ga_xIn_{1-x}As_yP_{1-y}$ on GaAs over the entire composition range
G. Zhang, M. Pessa, K. Hjelt, H. Collan and T. Tuomi 607
Inducement of GaAs growth by electron beam irradiation on GaAs covered by native oxide
K. Watanabe, M. Hosoya, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto 612
Study on dimer density evolution during GaAs short-pulse supersonic nozzle beam epitaxy on $(2\times4)\gamma$ initial surface by millisecond time-resolved reflectance difference
J. Cui, S. Zhang, A. Tanaka and Y. Aoyagi 616
Fast reconstruction transitions and fast surface reactions in short-pulse supersonic nozzle beam epitaxy
S. Zhang, J. Cui, A. Tanaka and Y. Aoyagi 622
Chemical beam epitaxial growth of InGaAs on GaAs(100) using triethylgallium, trimethylindium and unprecracked monoethylarsine
J.-R. Ro, S.-J. Park, S.-B. Kim and E.-H. Lee 627
Growth of $Ga_xIn_{1-x}As$/InP thin layer structures by chemical beam epitaxy
M.R. Leys, R.T.H. Rongen, J. Hopkins, H. Vonk, C.M. van Es, J.H. Wolter and F.D. Tichelaar 633
The etching effect of trisdimethylaminoantimony on (001) planar substrates
A.B. Villaflor, H. Asahi, D. Marx, K. Miki, K. Yamamoto and S. Gonda 638
The use of diethylsulphide for the doping of GaAs, AlGaAs and InGaAs grown by chemical beam epitaxy
T.B. Joyce, T.L. Pfeffer, T.J. Bullough, G. Petkos, P.J. Goodhew and A.C. Jones 644

SECTION X. GaAs ON Si AND RELATED STRUCTURES

Effect of the AlAs surface reconstruction on properties of Ge grown on AlAs
T. Maeda, H. Tanaka, M. Takikawa and K. Kasai 649
Rearrangement of misfit dislocations in GaAs on Si by post-growth annealing
M. Tamura, T. Yodo, T. Saitoh and J. Palmer 654
Effect of atomic hydrogen irradiation in low-temperature GaAs/Si heteroepitaxy
S. Ohta, Y. Okada and M. Kawabe 661
Initial growth of GaAs on vicinal Si(110) substrates
T. Yodo, M. Tamura and T. Saitoh 665
Selective growth of micro GaAs dots on Si by molecular beam epitaxy
H. Maeda, S. Watatani, H. Nakayama and T. Nishino 671
Suppression of threading dislocation generation in GaAs-on-Si with strained short-period superlattices
Y. Takagi, H. Yonezu, T. Kawai, K. Hayashida, K. Samonji, N. Ohshima and K. Pak 677
Reduction of dislocation density by thermal annealing for GaAs/GaSb/Si heterostructure
H. Uchida, T. Soga, H. Nishikawa, T. Jimbo and M. Umeno 681
GaAs on Si(111) with a layered structure GaSe buffer layer
J.E. Palmer, T. Saitoh, T. Yodo and M. Tamura 685
Migration-enhanced pulsed chemical beam epitaxy of GaP on Si(001)
N. Dietz, A. Miller, J.T. Kelliher, D. Venables and K.J. Bachmann 691
Growth and characterization of GaAs/Si/GaAs heterostructures
J.V. Thordson, P. Songpongs, G. Swenson and T.G. Andersson 696

SECTION XI. II–VI MATERIALS AND DEVICES

ZnMgSSe based laser diodes
S. Itoh and A. Ishibashi 701

Growth of ZnS and ZnSSe by gas-source molecular beam epitaxy using hydride group VI sources
M. Imaizumi, Y. Endoh, M. Suita, K. Ohtsuka, T. Isu and M. Nunoshita 707
Recombination mechanisms in photopumped $Zn_{1-x}Cd_xSe/ZnSe$ multiple quantum well lasers
L. Calcagnile, M. Di Dio, M. Lomascolo, R. Rinaldi, P. Prete, R. Cingolani, L. Vanzetti, A. Bonanni, F. Bassani, L. Sorba and A. Franciosi 712
Blue and green light-emitting diode structures grown by molecular beam epitaxy on ZnSe substrates
D. Eason, J. Ren, Z. Yu, C. Hughes, J.W. Cook, Jr., J.F. Schetzina, N.A. El-Masry, G. Cantwell and W.C. Harsh 718
Growth and characterization of wide bandgap $Zn_{1-x}Hg_xSe$
K. Hara, H. Machimura, M. Usui, H. Munekata, H. Kukimoto and J. Yoshino 725
p-Type and n-type doping of ZnSe: effects of hydrogen incorporation
P.A. Fisher, E. Ho, J.L. House, G.S. Petrich, L.A. Kolodziejski, J. Walker and N.M. Johnson 729
Metalorganic molecular beam epitaxy growth of ZnSe with new Zn and Se precursors without precracking
G. Sato, T. Numai, M. Hoshiyama, I. Suemune, H. Machida and N. Shimoyama 734
Growth of ZnSe/ZnMgSSe quantum well structures by metalorganic molecular beam epitaxy under in situ observation of reflection high energy electron diffraction intensity oscillation
J. Suda, Y. Kawakami, Sz. Fujita and Sg. Fujita 738
Structural and electrical properties of ZnSe laser diodes optimized by transmission electron microscopy, reflection high energy electron diffraction, X-ray diffraction and C–V profiling
T. Behr, D. Hommel, H. Cerva, J. Nürnberger, V. Beyersdorfer and G. Landwehr 743
Dependence of the structural properties of ZnSe on GaAs substrate orientation
P.J. Parbrook, M. Ishikawa, Y. Nishikawa, S. Saito, M. Onomura and G. Hatakoshi 749
Optimum growth conditions of molecular beam epitaxial growth of ZnSe at a low temperature
N. Matsumura, K. Maemura, N. Takanaka, S. Ichikawa and J. Saraie 755
Molecular beam epitaxial growth and characterization of ZnSTe epilayers and ZnSTe/ZnSe superlattices on Si substrates
Y.W. Chan, H. Wang, I.K. Sou, K.S. Wong and G.K.L. Wong 760
Influence of growth parameters on the properties of ZnSe–GaAs(001) heterostructures
L. Vanzetti, A. Bonanni, G. Bratina, L. Sorba, A. Franciosi, M. Lomascolo, D. Greco and R. Cingolani 765
Green emission enhanced by Te isoelectronic traps in ZnSe grown by molecular beam epitaxy
N. Takojima, Y. Ishizuka, I. Tsubono, N. Kimura, K. Suzuki, T. Sawada and K. Imai 770
Structural investigation of II–VI compound semiconductor quantum wires using triple-axis X-ray diffractometry
A.A. Darhuber, H. Straub, S. Ferreira, W. Faschinger, E. Koppensteiner, G. Brunthaler and G. Bauer 775
Molecular beam epitaxy grown CdTe/α-Sn/CdTe single quantum well structures
A.B. Villaflor, K. Shimomura, K. Kawamura, A.I. Belogorokhov and M. Kimata 779
Crystallinity improvement of HgCdTe on GaAs grown by molecular beam epitaxy
T. Sasaki, M. Tomono and N. Oda 785

SECTION XII. DOPING IN II–VI MATERIALS

The development of low voltage room temperature continuous wave laser diodes
R.L. Gunshor, J. Han, A.V. Nurmikko and A. Salokatve 790
Lowering of band-gap energy in heavily nitrogen-doped ZnSe
Z. Zhu, K. Takebayashi, T. Yao and Y. Okada 797
Growth and characterization of N-doped ZnS_xSe_{1-x} ($0 \leqq x < 0.3$) by molecular beam epitaxy
N. Teraguchi, S. Hirata, H. Mouri, Y. Tomomura, A. Suzuki and H. Takiguchi 803
Thermal stability of nitrogen-doped ZnSe grown by molecular beam epitaxy
Y. Nishikawa, M. Ishikawa, P.J. Parbrook, M. Onomura, S. Saito and G. Hatakoshi 807
Characterization of N-doped MgZnSSe compound system grown on intentionally misoriented GaAs substrates by molecular beam epitaxy
Y. Ichimura, K. Kishino, M. Satake, M. Kuramoto and A. Yoshida 812
Li-acceptor doping in ZnS/GaAs by post-heated molecular beam epitaxy
M. Yoneta, H. Saito, M. Ohishi, K. Kitani, H. Kobashi and C. Hatano 817
Reflection high-energy electron diffraction study of the heterointerface formation of ZnSe/ZnTe
T. Yao, M. Fujimoto, K. Uesugi, S. Kamiyama and Z. Zhu 823
Reduction of p-ZnSe/p-GaAs non-ohmic barrier by inserting a GaN buffer layer
Y. Hishida, T. Yoshie, K. Yagi, T. Yamaguchi and T. Niina 828
Gas source molecular beam epitaxy growth of InAlP band offset reduction layers on p-type ZnSe
K. Iwata, H. Asahi, J.H. Kim, X.F. Liu, S. Gonda, Y. Kawaguchi, A. Ohki and T. Matsuoka 833

SECTION XIII. ANTIMONIDE STRUCTURES

Accurate control of As and Sb incorporation ratio during solid-source molecular-beam epitaxy
Y.-H. Zhang 838
Electrical and photoluminescence properties of undoped GaSb prepared by molecular beam epitaxy and atomic layer molecular beam epitaxy
A. Bosacchi, S. Franchi, P. Allegri, V. Avanzini, A. Baraldi, C. Ghezzi, R. Magnanini, A. Parisini and L. Tarricone 844
(111) InAs/GaInSb strained-layer superlattice growth investigation
D.A. Reich, A.M. Wowchak, P.P. Chow and J.M. Van Hove 849
The n-type and p-type doping of GaSb and AlGaSb grown by metalorganic molecular beam epitaxy
K. Yamamoto, H. Asahi, K. Inoue, K. Miki, X.F. Liu, D. Marx, A.B. Villaflor, K. Asami and S. Gonda 853
Optical and structural investigations of intermixing reactions at the interfaces of InAs/AlSb and InAs/GaSb quantum wells grown by molecular-beam epitaxy
J. Schmitz, J. Wagner, F. Fuchs, N. Herres, P. Koidl and J.D. Ralston 858
Formation of InSb nanocrystals on Se-terminated GaAs(001)
Y. Watanabe, F. Maeda and M. Oshima 863
A Raman scattering study on the interface sharpness of InAs/AlSb/GaSb/AlSb polytype superlattices grown by molecular beam epitaxy
M. Yano, T. Utatsu, Y. Iwai and M. Inoue 868
Metalorganic molecular beam epitaxy of GaSb on patterned GaSb substrates using triethylgallium and Sb_4
D. Marx, K. Miyamoto, H. Asahi, X.F. Liu, A.B. Villaflor, K. Miki, S. Gonda, S. Shimomura and S. Hiyamizu 874
Structural and transport properties of InAs/AlSb superlattices
D.H. Chow, Y.H. Zhang, R.H. Miles and H.L. Dunlap 879
Hole accumulation in (In)GaSb/AlSb quantum wells induced by the Fermi-level pinning of an InAs surface
T. Makimoto, B. Brar and H. Kroemer 883

SECTION XIV. NITRIDE STRUCTURES

GaN based III–V nitrides by molecular beam epitaxy
H. Morkoç, A. Botchkarev, A. Salvador and B. Sverdlov 887
The growth and properties of group III nitrides
C.T. Foxon, T.S. Cheng, S.V. Novikov, D.E. Lacklison, L.C. Jenkins, D. Johnston, J.W. Orton, S.E. Hooper, N. Baba-Ali, T.L. Tansley and V.V. Tret'yakov 892
Effects of V/III supply ratio on improvement of crystal quality of zincblende GaN grown by gas source molecular beam epitaxy using RF-radical nitrogen source
A. Kikuchi, H. Hoshi and K. Kishino 897
Analysis and optimization of the electron cyclotron resonance plasma for nitride epitaxy
A. Ohtani, K.S. Stevens, M. Kinniburgh and R. Beresford 902
GaN growth by a controllable RF-excited nitrogen source
J.M. Van Hove, G.J. Cosimini, E. Nelson, A.M. Wowchak and P.P. Chow 908
Molecular beam epitaxy of gallium nitride by electron cyclotron resonance plasma and hydrogen azide
D.B. Oberman, H. Lee, W.K. Götz and J.S. Harris, Jr. 912
In situ monitoring of reflection high-energy electron diffraction oscillation during the growth of gallium nitride films by gas-source molecular beam epitaxy
Y. Moriyasu, H. Goto, N. Kuze and M. Matsui 916

SECTION XV. GROUP IV MBE

Prospects of SiGe heterodevices
E. Kasper 921
Elongated dimer structure for Ge overlayers on Si(001): symmetric or asymmetric?
H. Oyanagi, K. Sakamoto, R. Shioda and T. Sakamoto 926
Local structure of strain-compensated epitaxial $Si_{1-x-y}Ge_xC_y$ layers on Si(001) grown with molecular beam epitaxy
H.J. Osten, B. Dietrich, H. Rücker and M. Methfessel 931
Low-temperature heteroepitaxial growth of cubic SiC on Si using hydrocarbon radicals by gas source molecular beam epitaxy
T. Hatayama, Y. Tarui, T. Fuyuki and H. Matsunami 934

Suppression of Ge surface segregation during Si molecular beam epitaxy by atomic and molecular hydrogen irradiation
K. Nakagawa, A. Nishida, Y. Kimura and T. Shimada 939
Surfactant effect of H atoms on the suppression of Ge segregation in Si overgrowth on Ge(n ML)/Si(100) substrates by gas source molecular beam epitaxy
S. Zaima, K. Sato, T. Kitani, T. Matsuyama, H. Ikeda and Y. Yasuda 944
Growth and characterization of Si/SiGe microstructures on patterned Si substrates using gas source molecular beam epitaxy
J. Zhang, X.M. Zhang, A. Matsumura, A. Marinopoulou, J. Hartung, N. Anwar, G. Parry, M.H. Xie, S.M. Mokler, J.M. Fernández and B.A. Joyce 950
Atom-rearrangement in Ge layer grown on Si substrate during anneal observed in real time by coaxial impact collision ion scattering spectroscopy
T. Saitoh, M. Tamura, J.E. Palmer and T. Yodo 955
A scanning tunneling microscopy study of epitaxial Ge growth
F. Tsui, D. Barlett, J. Wellman, C. Uher and R. Clarke 960
Molecular beam epitaxy growth of Ge on Si(111) substrates covered by a SiO_2 mask
X. Zhang, H. Lu, D. Gong, X. Lu, X. Chen, J. Hu, W. Huang, Y. Fan and X. Wang 964
Selective epitaxial growth of Ge and SiGe using Si_2H_6 gas and Ge solid source molecular beam epitaxy
H. Wado, T. Shimizu, S. Ogura, M. Ishida and T. Nakamura 969
Phase transformation of crystallinity of $Si_{1-x}Ge_x$ layers grown on Si(001) by low temperature molecular beam epitaxy
S.-C. Lee, J.Y. Lee and S.J. Yun 974
Simultaneous Si molecular beam epitaxy and high-dose ion implantation
Y. Ishikawa and N. Shibata 980
Low temperature silicon epitaxy using supersonic molecular beams
R. Malik, E. Gulari, S.H. Li, P.K. Bhattacharya and J. Singh 984
Temperature dependence of boron surface segregation in Si molecular beam epitaxial growth on the Si(111) $\sqrt{3} \times \sqrt{3}$-B surface
Y. Kumagai, K. Ishimoto, R. Mori and F. Hasegawa 989
Kinetics of arsenic doping in silicon by ultra-high-vacuum chemical vapor deposition
N. Sugiyama, S. Imai and Y. Kawaguchi 994
The effect of in situ boron doping on the strain relaxation of $Si_{0.8}Ge_{0.2}$:B/Si heterostructure grown by molecular beam epitaxy
S.-C. Lee, S.J. Yun and J.Y. Lee 999
Epitaxial growth of $Si_{1-x-y}Ge_xC_y$ by ultrahigh vacuum chemical vapor deposition using disilane, germane and acetylene
M. Hiroi and T. Tatsumi 1005
Growth and properties of high-mobility two-dimensional hole gases in Ge on relaxed Si/SiGe, Ge/SiGe buffers and Ge substrates
J.F. Nützel, C.M. Engelhardt, R. Wiesner, D. Többen, M. Holzmann and G. Abstreiter 1011
Reflectance anisotropy and reflection high-energy electron diffraction intensity oscillations during gas source molecular beam epitaxy growth of Si and SiGe on Si(001)
J. Zhang, A.G. Taylor, J.M. Fernández, B.A. Joyce, A.R. Turner and M.E. Pemble 1015
Characterization of termination layer of SiGe system through signatures of Si–O and Ge–O species
K. Prabhakaran and T. Ogino 1020

SECTION XVI. GROUP IV QUANTUM WELLS, WIRES AND DOTS

Luminescence of strained $Si_{1-x}Ge_x$/Si quantum wells and microstructures
S. Fukatsu and Y. Shiraki 1025
Crucial role of Si buffer layer quality in the photoluminescence efficiency of strained $Si_{1-x}Ge_x$/Si quantum wells
T. Mine, N. Usami, Y. Shiraki and S. Fukatsu 1033
Photoluminescence investigation on growth mode changeover in Ge-rich $Si_{1-x}Ge_x$/Si strained quantum wells
H. Sunamira, S. Fukatsu and Y. Shiraki 1038
Band-gap luminescence in strain-symmetrized Si_m/Ge_n superlattices grown by molecular beam epitaxy using gaseous Si_2H_6 and solid Ge
X. Zhu, Q. Xiang, M. Chu and K.L. Wang 1045
SiGe quantum wells on (110) Si grown by molecular beam epitaxy
J. Brunner, M. Gail, G. Abstreiter and P. Vogl 1050
Cavity mode luminescence of strained $Si_{1-x}Ge_x$/Si quantum wells grown on a buried-oxide substrate
S. Fukatsu, D.K. Nayak and Y. Shiraki 1055

SiGe wires and dots grown by local epitaxy
J. Brunner, P. Schittenhelm, J. Gondermann, B. Spangenberg, B. Hadam, T. Köster, H.G. Roskos, H. Kurz, H. Gossner, I. Eisele and G. Abstreiter 1060
Strain-induced lateral band gap modulation in $Si_{1-x}Ge_x$/Si quantum well and quantum wire structures
N. Usami, H. Sunamura, T. Mine, S. Fukatsu and Y. Shiraki 1065
Cathodoluminescence investigation of SiGe quantum wires fabricated on V-groove patterned Si substrates
V. Higgs, E.C. Lightowers, N. Usami, Y. Shiraki, T. Mine and S. Fukatsu 1070

SECTION XVII. OXIDES AND FLUORIDES

Effect of adjacent insulating oxide layers on superconductivity of one unit cell thick $YBa_2Cu_3O_{7-\delta}$ layers in $PrBa_2Cu_3O_{7-\delta}/YBa_2Cu_3O_{7-\delta}$/insulating oxide trilayers
Y. Bando, T. Terashima, K. Shimura, Y. Daitoh and Y. Yano 1074
Low-temperature nucleation and the heteroepitaxial growth of ultra-thin films of Sr and Ba oxides
G. Pindoria, K. Kawaguchi, M. Nishiyama and T. Morishita 1080
Preparation of $BaBiO_3$ thin films using an oxygen radical beam source
M. Iyori, S. Suzuki, K. Yamano, H. Suzuki, K. Takahashi and Y. Yoshisato 1086
Ferroelectric phase transition in $BaTiO_3$ films
Y. Yoneda, H. Kasatani, H. Terauchi, Y. Yano, T. Terashima and Y. Bando 1090
$Bi_2Sr_2Ca_{n-1}Cu_nO_y$ thin films by growth interruption technique
T. Ishibashi, H. Soutome, Y. Okada and M. Kawabe 1094
Ordering of sulfur interlayer in molecular beam epitaxy-grown SrF_2/S/GaAs(110)A and B
M. Sugiyama, S. Maeyama, Y. Watanabe, S. Heun and M. Oshima 1098
Characterization of ferroelectric $BaMgF_4$ films grown on AlGaAs/GaAs(100) high-electron-mobility transistor structures
S. Ohmi, E. Tokumitsu and H. Ishiwara 1104
Morphology of thin SrF_2 films on InP(111) studied by reflection high-energy electron diffraction
S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 1108
High-quality CdF_2 layer growth on CaF_2/Si(111)
A. Izumi, K. Tsutsui, N.S. Sokolov, N.N. Faleev, S.V. Gastev, S.V. Novikov and N.L. Yakovlev 1115
Growth by molecular beam epitaxy and structural study of lattice matched $Mg_xCa_{1-x}F_2$ films on silicon
N.L. Yakovlev and Yu.V. Shusterman 1119
X-ray absorption fine structure studies of sulfur interlayers in molecular beam epitaxy grown SrF_2/S/GaAs(111)
S. Maeyama, M. Sugiyama, S. Heun and M. Oshima 1122

SECTION XVIII. MAGNETIC MATERIALS, METALS III–VI, IV–VI, CHALCOPYRITE, AND OTHERS

Magnetic superlattices: molecular beam epitaxial growth and properties of artificially and naturally-layered structures
R.F.C. Farrow, R.F. Marks, A. Cebollada, G.R. Harp, T.A. Rabedeau, M.F. Toney, D. Weller and S.S.P. Parkin 1126
Heteroepitaxy of ferromagnetic MnAs thin films on (001) GaAs: template effects and epitaxial orientations
M. Tanaka, J.P. Harbison and G.M. Rothberg 1132
Epitaxial ferromagnetic (τ MnAl/Co) and (Co/CoAl) multilayers on GaAs (001) grown by molecular beam epitaxy
J. De Boeck, C. Bruynseraede, H. Bender, A. Van Esch, W. Van Roy and G. Borghs 1139
Fabrication and magneto-optical properties of epitaxial ferromagnetic $Mn_{1-x}Sb$ thin films grown on GaAs and sapphire
H. Akinaga, K. Tanaka, K. Ando and T. Katayama 1144
Epitaxial growth of thick pseudomorphic NiAl metal films on GaAs by migration enhanced epitaxy
M.V. Weckwerth, C.Y. Hung, Y.C. Pao and J.S. Harris, Jr. 1150
Elastic anomalies in single crystal copper/nickel superlattices grown by molecular beam epitaxy
K. Sakaue, N. Sano, H. Terauchi and A. Yoshihara 1154
Al growth on Si(001) observed by scanning tunneling microscopy
N. Shimizu, H. Kitada and O. Ueda 1159
Initial stages of Ag growth on Sb-terminated GaAs(001)
F. Maeda, Y. Watanabe and M. Oshima 1164
Gold growth on Si(111) $\sqrt{3} \times \sqrt{3}$ Ag and $\sqrt{3} \times \sqrt{3}$ Au surfaces
A. Ichimiya, H. Nomura, Y. Ito and H. Iwashige 1169
Molecular beam epitaxial growth and characterization of epitaxial GaSe films on (001)GaAs
N. Kojima, K. Sato, M. Budiman, A. Yamada, M. Konagai, K. Takahashi, Y. Nakamura and O. Nittono 1175

Van der Waals epitaxy on hydrogen-terminated Si(111) surfaces and investigation of its growth mechanism by atomic force microscope
K. Ueno, M. Sakurai and A. Koma 1180
Thermal mismatch strain relaxation of epitaxial IV–VI/Si(111) structures on multiple temperature cycling to cryogenic temperatures
H. Zogg and S. Teodoropol 1186
A novel method for the study of strain relaxation in lattice-mismatched heteroepitaxy: ultra-high vacuum scanning tunneling microscopy combined with in situ reflection high-energy electron diffraction
N. Frank, G. Springholz and G. Bauer 1190
Characterization of molecular beam epitaxy grown $CuInSe_2$ on GaAs(001)
R. Shioda, Y. Okada, H. Oyanagi, S. Niki, A. Yamada and Y. Makita 1196
Heteroepitaxy and characterization of $CuInSe_2$ on GaAs(001)
S. Niki, Y. Makita, A. Yamada, O. Hellman, P.J. Fons, A. Obara, Y. Okada, R. Shioda, H. Oyanagi, T. Kurafuji, S. Chichibu and H. Nakanishi 1201
Stoichiometric control of $CuInSe_2$ thin films using a molecular beam epitaxy technique
B.-H. Tseng, S.-B. Lin, K.-C. Hsieh and H.-L. Hwang 1206
Blue luminescent $SrGa_2S_4$:Ce thin films grown by molecular beam epitaxy
K. Tanaka, Y. Inoue, S. Okamoto and K. Kobayashi 1211

SECTION XIX. ELECTRONIC DEVICES

The effect of growth temperature, δ-doping and barrier composition on mobilities in shallow AlGaAs–GaAs two-dimensional electron gases
M.C. Holland, E. Skuras, J.H. Davies, I.A. Larkin, A.R. Long and C.R. Stanley 1215
Enhancement of electron mobility by preventing pit formation at the $In_{0.52}Al_{0.48}As/In_{0.8}Ga_{0.2}As$ heterointerface using an inserted $In_{0.53}Ga_{0.47}As$ layer
T. Nakayama, H. Miyamoto, E. Oishi and N. Samoto 1220
InP-based heterostructure field-effect transistors with high-quality short-period $(InAs)_{3m}/(GaAs)_{1m}$ superlattice channel layers
U. Auer, R. Reuter, C. Heedt, W. Prost and F.J. Tegude 1225
High G_m $In_{0.5}Al_{0.5}As/In_{0.5}Ga_{0.5}As$ high electron mobility transistors grown lattice-mismatched on GaAs substrates
T. Mishima, K. Higuchi, M. Mori and M. Kudo 1230
Highly strained InGaAs layers on GaAs grown by molecular beam epitaxy for high electron mobility transistors
M. Kudo, T. Mishima and M. Washima 1236
Optimized molecular beam epitaxial growth temperature profile for high-performance AlInAs/GaInAs single quantum well high electron mobility transistor structures
H. Künzel, J. Böttcher, A. Hase, S. Strähle and E. Kohn 1241
Effect of strained layer on GaAs power field effect transistor using low temperature buffer
S. Sano, E. Heidarpour, K. Nanbu, T. Igarashi, J. Saito and T. Matsumoto 1246
Molecular beam epitaxial growth of pseudomorphic InAlAs/InGaAs high electron mobility transistors with high cut-off frequencies
W. Klein, G. Böhm, H. Heiss, S. Kraus, D. Xu, R. Semerad, G. Tränkle and G. Weimann 1252
Growth conditions and device performance of InGaAs/AlGaAs pseudomorphic inverted high electron mobility transistor
T. Kawaguchi, M. Sato, H.I. Fujishiro and S. Nishi 1256
Growth of high-quality InGaP and application for modulation-doped structure by molecular beam epitaxy with a GaP source
T. Shitara, K. Eberl, J. Dickmann and C. Wölk 1261
Electron distribution in modulation doped AlGaAs/GaAs single quantum wells and inverted modulation doped GaAs/AlGaAs heterostructures
K. Suzuki, K. Saito, T. Saku, A. Sugimura, Y. Horikoshi and S. Yamada 1266
Backgating and light sensitivity in GaAs metal–semiconductor field effect transitors
R.-G. Li, Z.-G. Wang, J.-B. Liang, G.-B. Ren, T.-W. Fan and L.-Y. Lin 1270
GaAs-based metal–insulator–semiconductor structures with low interface traps using molecular beam epitaxy and chemical vapor deposition
D.G. Park, M. Tao, J. Reed, K. Suzue, A.E. Botchkarev, Z. Fan, G.B. Gao, S.J. Chey, J. Van Nostrand, D.G. Cahill and H. Morkoç 1275

High current gain InGaP/GaAs heterojunction bipolar transistors grown by multi-wafer gas-source molecular beam epitaxy system
H. Ando, N. Okamoto, S. Yamaura, T. Tomioka, T. Takahashi, H. Shigematsu, A. Kawano, S. Sasa and T. Fujii 1281
Quantitative correlation between oxygen impurity and current gain β of AlGaAs/GaAs heterojunction bipolar transistors grown by molecular beam epitaxy
S. Izumi, M. Sakai, T. Shimura, M. Tsugami, N. Hayafuji, T. Sonoda, S. Takamiya, W. Susaki and S. Mitsui 1287
Continuous molecular beam epitaxy of arsenides and phosphides applied to device structures on InP substrates
J.C. Harmand, J.P. Praseuth, E. Idiart-Alhor, R. Palla, J.L. Pelouard and M. Quillec 1292
Molecular beam epitaxy growth for a heavily-doped thin base layer of heterojunction bipolar transistors used for high-speed integrated circuits
N. Iizuka, K. Tsuda, T. Nozu, T. Sugiyama, Y. Kuriyama and M. Obara 1297
High sensitivity Hall elements made from Si-doped InAs on GaAs substrates by molecular beam epitaxy
T. Iwabuchi, T. Ito, M. Yamamoto, K. Sako, Y. Kanayama, K. Nagase, T. Yoshida, F. Ichimori and I. Shibasaki 1302
InAs deep quantum well structures and their application to Hall elements
N. Kuze, K. Nagase, S. Muramatsu, S. Miya, T. Iwabuchi, A. Ichii and I. Shibasaki 1307

SECTION XX. OPTICAL DEVICES

Molecular beam epitaxy growth of an ultrahigh finesse microcavity
U. Oesterle, R.P. Stanley, R. Houdré, M. Gailhanou and M. Ilegems 1313
Integration of single/double vertical-cavity devices by mask molecular beam epitaxy
H. Saito, H. Kosaka, Y. Sugimoto and K. Kasahara 1318
Molecular beam epitaxy growth of lattice-matched AlGaInAs/GaInAs multiple quantum well distributed feedback laser structures with gratings defined by implantation enhanced intermixing
H. Künzel, J. Böttcher, A. Hase, V. Hofsäss, C. Kaden and H. Schweizer 1323
Molecular-beam-epitaxy growth of strained $Ga_{1-x}In_xAs$/AlInAs/InP and application to 1.55 μm multi-quantum-well lasers
K. Nishikata, H. Shimizu, Y. Hirayama, T. Matsuda, F. Iwase and M. Irikawa 1328
Reliable red-emitting laser diodes grown by solid source molecular beam epitaxy
K. Takahashi, T. Takeoka, Y. Kan, A. Tsunoda, K. Tani, M. Hosoda, S. Matsui and S. Yamamoto 1333
Growth of InGaAs/GaAs strained quantum wells on GaAs(111)B substrates and continuous wave operation of (111)-oriented InGaAs strained quantum well lasers
T. Takeuchi, K. Muraki, Y. Hanamaki, S. Fukatsu, N. Yamada, N. Ogasawara, N. Mikoshiba and Y. Shiraki 1338
Gas source molecular beam epitaxy growth of GaAs/InGaP superlattice as optical confinement layers in 0.98 μm InGaAs/InGaP strained quantum well lasers
M. Usami, Y. Matsushima and Y. Takahashi 1344
Use of molecular beam epitaxy for high-power AlGaAs laser production
V.P. Chaly, D.M. Demidov, G.A. Fokin, S.Yu. Karpov, V.E. Myachin, Yu.V. Pogorelsky, I.Yu. Rusanovich, A.P. Shkurko and A.L. Ter-Martirosyan 1350
2.78 μm InGaAsSb/AlGaAsSb multiple quantum-well lasers with metastable InGaAsSb wells grown by molecular beam epitaxy
H. Lee, P.K. York, R.J. Menna, R.U. Martinelli, D. Garbuzov and S.Y. Narayan 1354
Selective molecular beam epitaxial growth for multifunction microwave monolithic and opto-electronic integrated circuits
Y.C. Pao, J. Franklin and C. Shih 1358
Monolithic integration of 850 nm quantum well modulators to very large scale integrated electronics on GaAs
J.E. Cunningham, K.W. Goossen, W.Y. Jan, J.A. Walker and R.N. Pathak 1363
InAs/GaAs short-period strained-layer superlattice modulators grown using advanced digital reflection high-energy electron diffraction techniques
T.C. Hasenberg, P. Chen, A. Madhukar, A.R. Kost, J. Visher and A. Konkar 1368
Molecular beam epitaxial growth, characterization and performance of high-detectivity GaInAsSb/GaSb PIN detectors operating at 2.0 to 2.6 μm
A.Z. Li, J.Q. Zhong, Y.L. Zheng, J.X. Wang, G.P. Ru, W.G. Bi and M. Qi 1375
Enhanced electron transfer in real-space transfer devices using strained $In_xGa_{1-x}As$ ($x = 0.15, 0.25$) channel layers
J.-T. Lai and J.Y. Lee 1379

Triangular-barrier optoelectronic switch by gas source molecular beam epitaxy
H. Sakata, K. Utaka and Y. Matsushima 1384
Resonant-tunneling triangular-barrier optoelectronic switch by gas source molecular beam epitaxy
H. Sakata, K. Utaka and Y. Matsushima 1389

Author index 1395

Subject index 1416